

# HS-1254RH

## **PRELIMINARY**

**April 1998** 

## Radiation Hardened, High Speed, Low Power Dual Operational Amplifier with Disable

#### Features

- QML Qualified Per MIL-PRF-38535 Requirements
- Radiation Environment
- Low Quiescent Current (per amp) . . . . . 6.1mA (Max)
- Disabled Supply Current (per amp) . . . . 4.0mA (Max)
- Low Offset Voltage ......5.0mV (Max)
- Output Enable/Disable Time...... 160ns/20ns (Typ)
- High Slew Rate ...... 1050V/μs (Typ)
- Wide -3dB Bandwidth (A<sub>V</sub> = +2) . . . . . . 530MHz (Typ)

## **Applications**

- High Speed A/D Drivers
- Cable Drivers
- · Wideband Signal Switching and Routing
- Redundant Circuit Multiplexing
- Pulse Amplifiers

### Description

The HS-1254RH is a  $\pm$ 5V, Rad Hard, monolithic, dual, current feedback amplifier that provides highly reliable performance in harsh radiation environments. Dielectric isolation and bonded wafer processing make this device immune to latch-up (SEL).

Excellent dynamic characteristics, coupled with the disable function, make this amplifier well-suited for a variety of satellite system applications. The outputs have individual disable control pins that make it easy to multiplex wideband signals, putting the outputs in a high impedance mode and reducing the supply current per op amp down to 3mA (typical).

Post radiation limits are fully specified and guaranteed to 300kRAD(Si) total dose to ensure predictable performance in any space application.

Specifications for Rad Hard QML devices are controlled by the Defense Supply Center in Columbus (DSCC). SMD numbers must be used when ordering.

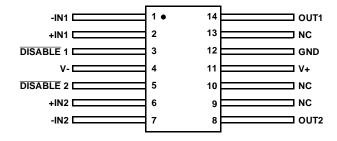
Detailed Electrical Specifications for the HS-1254RH are contained in SMD 5962-98581, which is easily downloadable from our website, via a DSCC "hot-link". http://www.semi.intersil.com/data/sm/index.htm

## **Ordering Information**

SMD PART NUMBER	INTERSIL PART NUMBER	TEMP. RANGE (°C)	PACKAGE	CASE OUTLINE	
5962R9858101VXC	HS9-1254RH-Q	-55 to 125	14 Ld Flatpack	CDFP3-F14	
N/A	HS9-1254RH/Sample	25	14 Ld Flatpack	CDFP3-F14	

#### **Pinout**

#### HS-1254RH (FLATPACK) TOP VIEW



## Die Characteristics

#### **DIE DIMENSIONS**

Size: 1750µm x 2330µm (69 mils x 92 mils)

Thickness: 483µm (19 mils)

#### **GLASSIVATION**

Type: Nitride

Thickness: 4kÅ ± 0.5kÅ

#### **METALLIZATION**

#### Metal 1

Type: AlCu(2%)/TiW Thickness: 8kÅ ± 0.4kÅ

#### Metal 2

Type: AICu(2%)

Thickness: 16kÅ ± 0.8kÅ

#### **SUBSTRATE**

DI, Bonded Wafer

#### **BACKSIDE FINISH**

Silicon

#### SUBSTRATE POTENTIAL

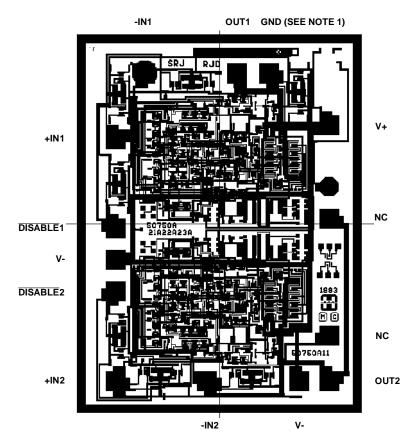
Floating (Recommend connection to V-)

#### TRANSISTOR COUNT:

180

## Metallization Mask Layout

#### HS-1254RH



#### NOTE:

1. This is an optional GND pad. Users may set a GND reference, via this pad, to ensure the TTL compatibility of the DISABLE inputs when using asymmetrical supplies (e.g., V+ = 10V, V- = 0V).



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## Sales Office Headquarters

## NORTH AMERICA

Intersil Corporation 7585 Irvine Center Drive Suite 100 Irvine, CA 92618 TEL: (949) 341-7000

FAX: (949) 341-7123

Intersil Corporation 2401 Palm Bay Rd. Palm Bay, FL 32905 TEL: (321) 724-7000 FAX: (321) 724-7946 **EUROPE** Intersil Europe Sarl Ave. William Graisse, 3 1006 Lausanne

Switzerland TEL: +41 21 6140560 FAX: +41 21 6140579

#### ASIA

Intersil Corporation
Unit 1804 18/F Guangdong Water Building
83 Austin Road
TST Kowloon Hong Kong

TST, Kowloon Hong Kong TEL: +852 2723 6339 FAX: +852 2730 1433